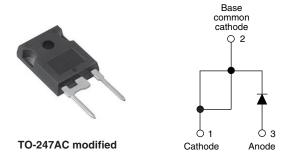


Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS						
I _{F(AV)}	30 A					
V_{R}	600 V					
V _F at I _F	1.34 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Package	TO-247AC modified					
Circuit configuration	Single					

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Single diode device
- Designed and qualified according to JEDEC®-JESD 47







ROHS COMPLIANT HALOGEN FREE

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V_{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 116 °C	30	^			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	300	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-			
Forward voltage	V _F	I _F = 30 A	-	2.0	2.6	V		
		I _F = 30 A, T _J = 150 °C	-	1.34	1.75			
D last	1	$V_R = V_R$ rated	-	0.3	50			
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	60	500	- μA		
Junction capacitance	C _T	V _R = 600 V	-	33	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	ı	3.5	-	nH		



VS-30EPH06PbF, VS-30EPH06-N3

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	28	35		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	31	-	ns	
		T _J = 125 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	77	-		
Dools recovery oursent	I _{RRM}	T _J = 25 °C		-	3.5	-	۸	
Peak recovery current		T _J = 125 °C		-	7.7	-	A	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		=	65	-	nC	
		T _J = 125 °C		-	345	-	IIC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	0.5	0.9		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.4	-		
Weight			-	6.0	-	g	
vveignt			-	0.22	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified		30EPH06			



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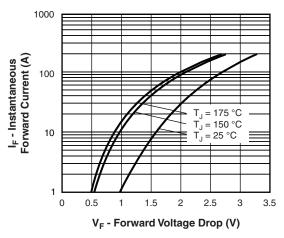


Fig. 1 - Typical Forward Voltage Drop Characteristics

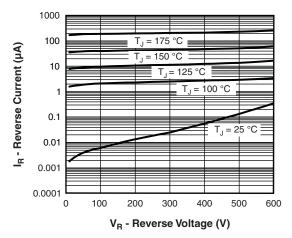


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

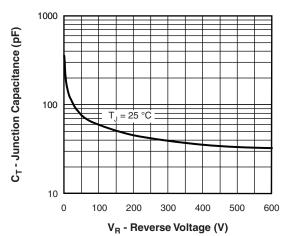


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

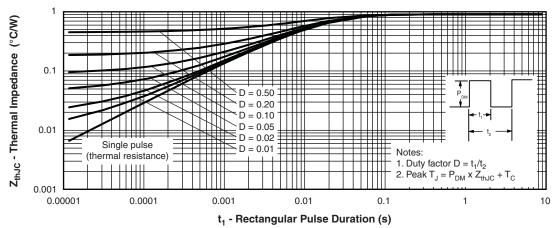


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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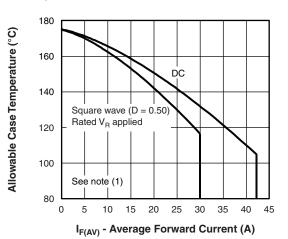


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

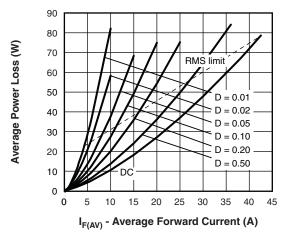


Fig. 6 - Forward Power Loss Characteristics

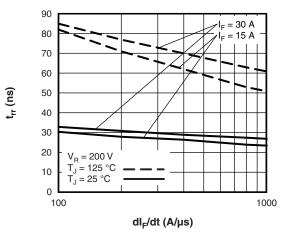


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

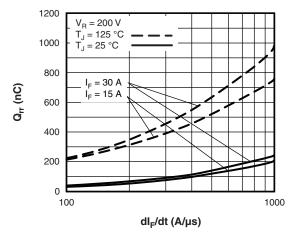


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

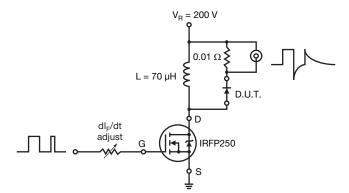
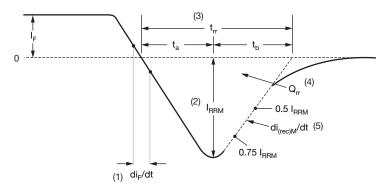


Fig. 9 - Reverse Recovery Parameter Test Circuit

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

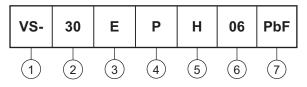
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (30 = 30 A)
- Circuit configuration:

E = single diode

- Package:
 - P = TO-247AC modified
- H = hyperfast recovery
- Voltage rating (06 = 600 V)
- Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-30EPH06PbF	25	500	Antistatic plastic tube			
VS-30EPH06-N3	25	500	Antistatic plastic tube			

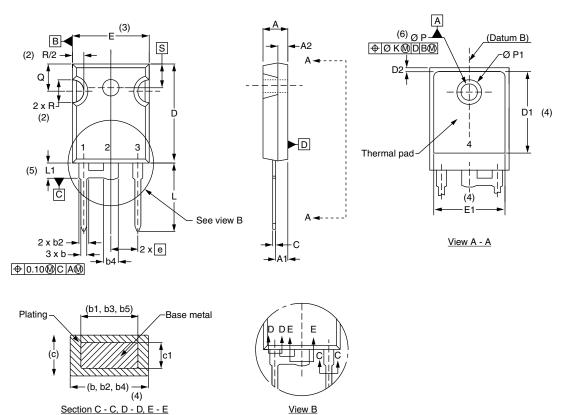
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95541					
Doub wood in a information	TO-247AC modified PbF	www.vishay.com/doc?95255			
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442			
SPICE model		www.vishay.com/doc?96573			



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TO-247AC modified - 50 mils L/F

DIMENSIONS in millimeters and inches



	,				,	
SYMBOL	MILLIN	MILLIMETERS		INCHES		
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.65	5.31	0.183	0.209		
A1	2.21	2.59	0.087	0.102		
A2	1.17	1.37	0.046	0.054		
b	0.99	1.40	0.039	0.055		
b1	0.99	1.35	0.039	0.053		
b2	1.65	2.39	0.065	0.094		
b3	1.65	2.34	0.065	0.092		
b4	2.59	3.43	0.102	0.135		
b5	2.59	3.38	0.102	0.133		
С	0.38	0.89	0.015	0.035		
c1	0.38	0.84	0.015	0.033		
D	19.71	20.70	0.776	0.815	3	
D1	13.08	-	0.515	-	4	

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
Е	15.29	15.87	0.602	0.625	3
E1	13.46	=.	0.53	-	
е	5.46	BSC	0.215	BSC	
ØK	0.2	0.254)10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	5.51 BSC		0.217 BSC	

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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